# **1SS83**

# Silicon Epitaxial Planar Diode for High Voltage Switching

# HITACHI

ADE-208-150A (Z) Rev. 1 Jul. 1995

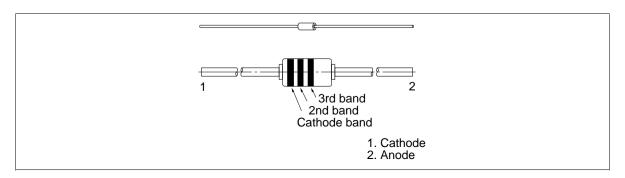
### Features

- High reverse voltage. ( $V_R = 250V$ )
- High reliability with glass seal.

# **Ordering Information**

Type No.	Cathode band	2nd band	3rd band	Package Code
1SS83	Verdure	Light Blue	Light Blue	DO-35

#### Outline





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# **Absolute Maximum Ratings**<sup>\*2</sup> (Ta = $25^{\circ}$ C)

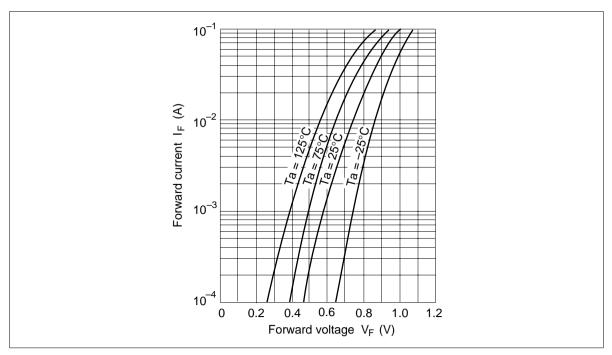
Item	Symbol	Value	Unit
Peak reverse voltage	$V_{RM}^{*1}$	300	V
Reverse voltage	V <sub>R</sub>	250	V
Peak forward current	I <sub>FM</sub>	625	mA
Non-Repetitive peak forward surge current	I <sub>FSM</sub> * <sup>2</sup>	1	A
Average forward current	I <sub>o</sub>	200	mA
Power dissipation	Pd	400	mW
Junction temperature	Тј	175	°C
Storage temperature	Tstg	-65 to +175	°C

Notes: 1. Reverse voltage in excess of peak reverse voltage may deteriorate electrical characteristic.

2. Within 1s forward surge current.

#### **Electrical Characteristics** (Ta = 25°C)

Item	Symbol	Min	Тур	Max	Unit	Test Condition
Forward voltage	V <sub>F</sub>	_	_	1.0	V	I <sub>F</sub> = 100mA
Reverse current	I <sub>R1</sub>	_	_	0.2	μΑ	V <sub>R</sub> = 250V
	I <sub>R2</sub>	—	—	100		V <sub>R</sub> = 300V
Capacitance	С	_	1.5	_	pF	$V_R = 0V$ , f = 1MHz
Reverse recovery time	t <sub>rr</sub>	—	—	100	ns	$I_F = I_R = 30$ mA, Irr = 3mA, $R_L = 100\Omega$





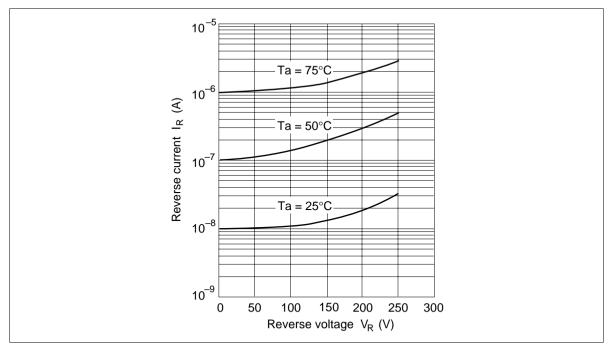


Fig.2 Reverse current Vs. Reverse voltage

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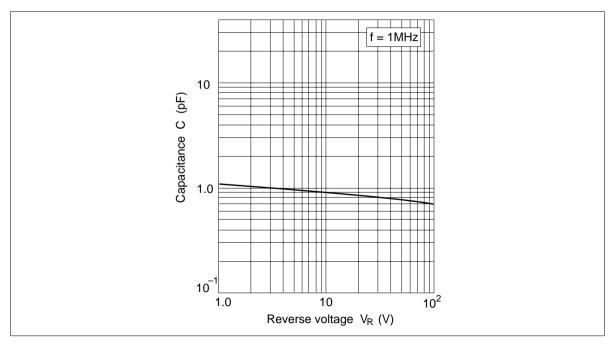
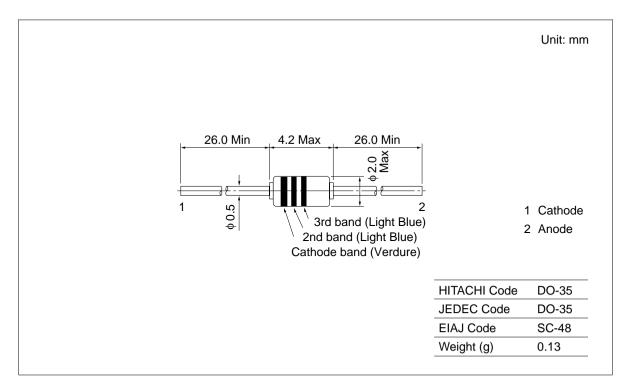


Fig.3 Capacitance Vs. Reverse voltage

# **Package Dimensions**



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